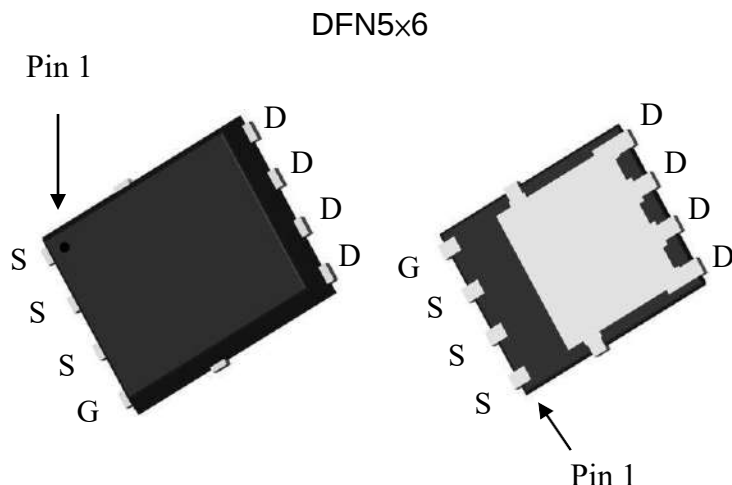


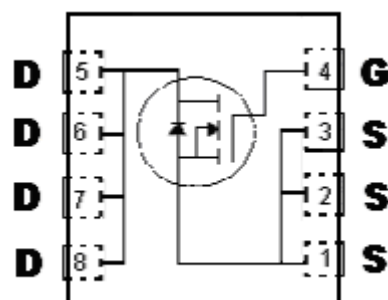
N-Channel Enhancement Mode Power MOSFET

Features:

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package



BV_{DSS}	150V
I_D@V_{GS}=10V, T_C=25°C	45A
I_D@V_{GS}=10V, T_A=25°C	8A
R_{DS(ON)}@V_{GS}=10V, I_D=20A	13mΩ(typ)



G : Gate D : Drain S : Source

Ordering Information

Device	Package	Shipping
KPRE012N15R	DFN 5 ×6 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	10s	Steady State	Unit
Drain-Source Voltage	V _{DS}	150		V
Gate-Source Voltage	V _{GS}	±20		
Continuous Drain Current @ T _C =25°C, V _{GS} =10V (Note 1)	I _D	45		A
Continuous Drain Current @ T _C =100°C, V _{GS} =10V (Note 1)		28.5		
Continuous Drain Current @ T _A =25°C, V _{GS} =10V (Note 2)	I _{DSM}	12	8	
Continuous Drain Current @ T _A =70°C, V _{GS} =10V (Note 2)		9.7	6.4	
Continuous Drain Current @ T _A =85°C, V _{GS} =10V (Note 2)		8.7	5.8	
Pulsed Drain Current (Note 3)	I _{DM}	132	*1	mJ
Avalanche Current @ L=0.1mH (Note 3)	I _{AS}	39		
Avalanche Energy @ L=1mH, I _D =20A, V _{DD} =25V (Note 4)	E _{AS}	200		
Repetitive Avalanche Energy @ L=0.05mH (Note 3)	E _{AR}	8	*2	W
Total Power Dissipation	P _D	78		
		31		
	P _{DSM}	5.7	2.5	
		4.0	1.8	
		3.6	1.6	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C

Thermal Data

Parameter	Symbol	Typical	Maximum	Unit
Thermal Resistance, Junction-to-ambient (Note 2)	R _{θJA}	18	22	°C/W
		42	50	
Thermal Resistance, Junction-to-case	R _{θJC}	1.3	1.6	

Note : 1.The power dissipation P_D is based on T_{J(MAX)}=150 °C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2.The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25 °C. The power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

3.Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150 °C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

4.100% tested by conditions of L=0.1mH, I_{AS}=12A, V_{GS}=10V, V_{DD}=25V

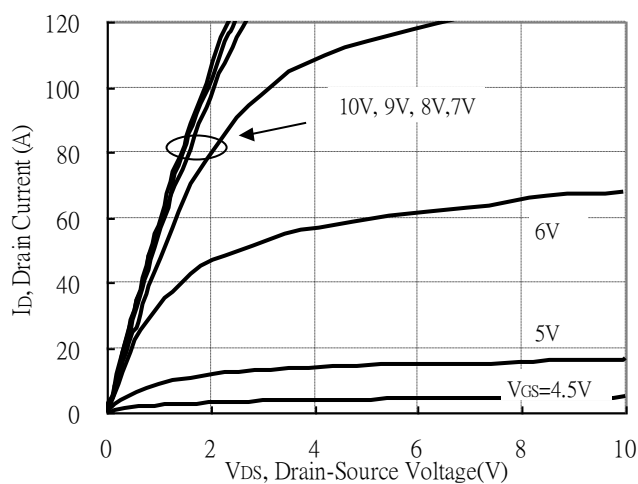
Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	150	-	-	V	V _{GS} =0V, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.12	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	2	-	4	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	21	-	S	V _{DS} =10V, I _D =20A
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =120V, V _{GS} =0V
	-	-	25		V _{DS} =120V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	13	17	mΩ	V _{GS} =10V, I _D =20A
Dynamic					
*Q _g	-	52.7	-	nC	V _{DS} =75V, I _D =20A, V _{GS} =10V
*Q _{gs}	-	16.4	-		
*Q _{gd}	-	15.3	-		
*t _{d(ON)}	-	30.4	-	ns	V _{DS} =75V, I _D =20A, V _{GS} =10V, R _{GS} =1Ω
*t _r	-	23	-		
*t _{d(OFF)}	-	50	-		
*t _f	-	14.2	-		
C _{iss}	-	3161	-	pF	V _{GS} =0V, V _{DS} =75V, f=1MHz
C _{oss}	-	220	-		
C _{rss}	-	48	-		
R _g	-	0.9	-	Ω	f=1MHz
Source-Drain Diode					
*I _S	-	-	45	A	
*I _{SM}	-	-	132		
*V _{SD}	-	0.8	1.2	V	I _S =10A, V _{GS} =0V
*t _{rr}	-	71.6	-	ns	V _{GS} =0V, I _F =10A, dI _F /dt=100A/μs
*Q _{rr}	-	208	-	nC	

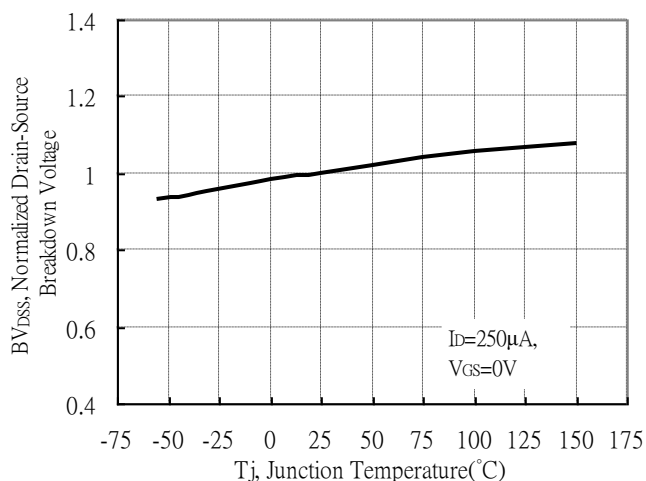
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

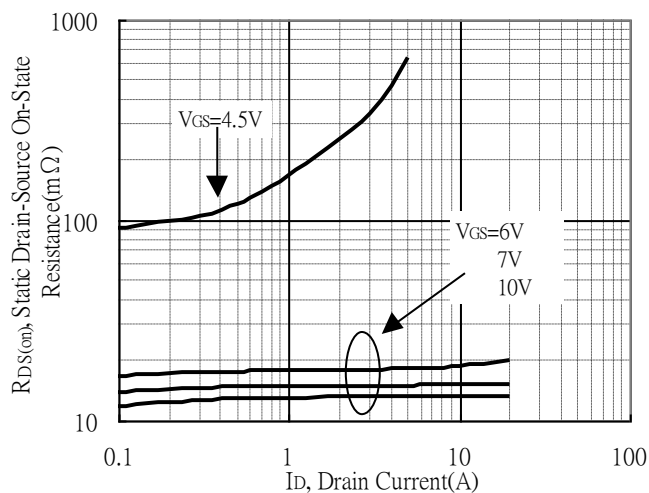
Typical Output Characteristics



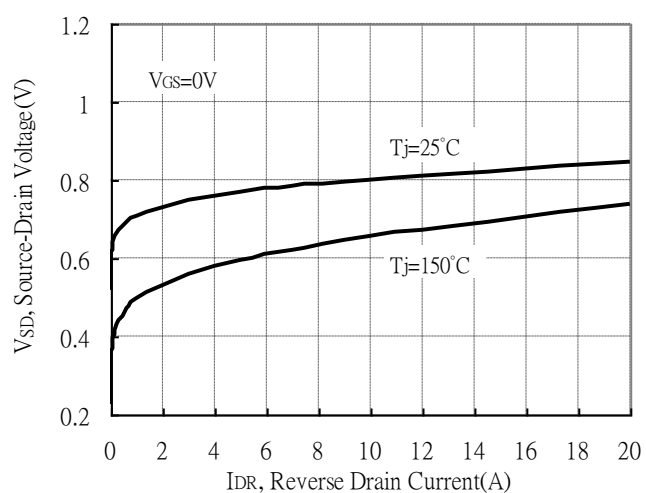
Breakdown Voltage vs Ambient Temperature



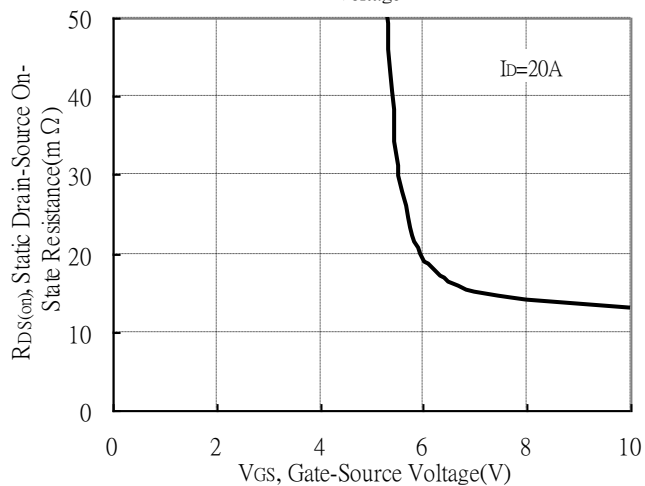
Static Drain-Source On-State resistance vs Drain Current



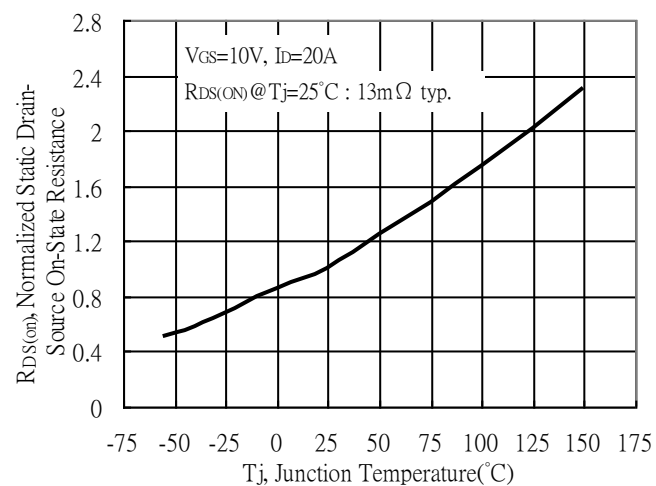
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

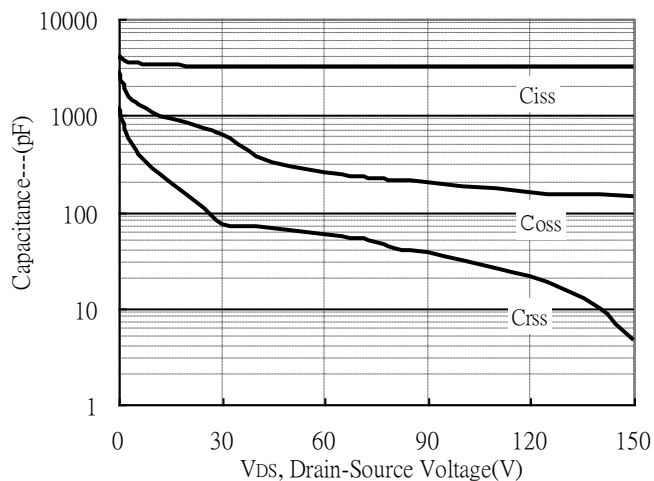


Drain-Source On-State Resistance vs Junction Temperature

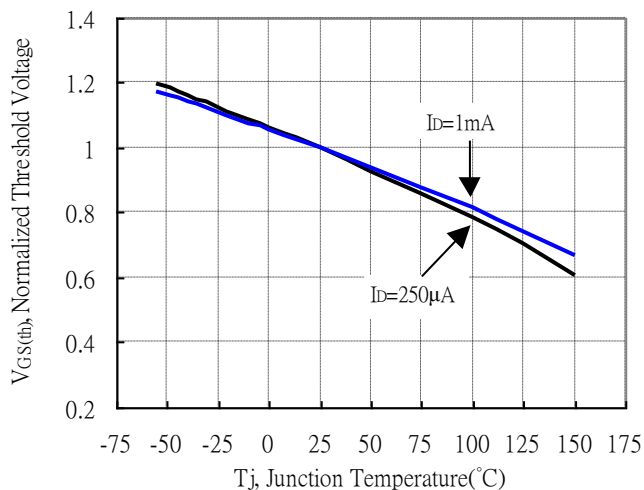


Typical Characteristics(Cont.)

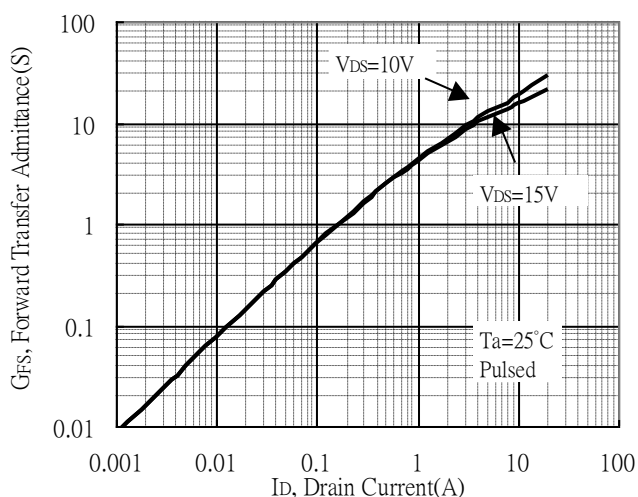
Capacitance vs Drain-to-Source Voltage



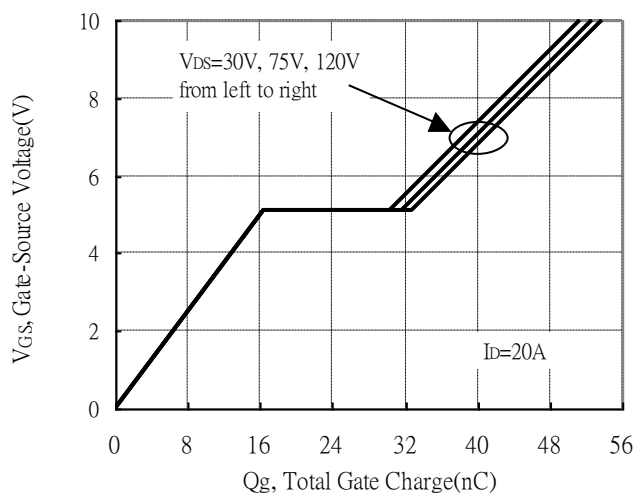
Threshold Voltage vs Junction Temperature



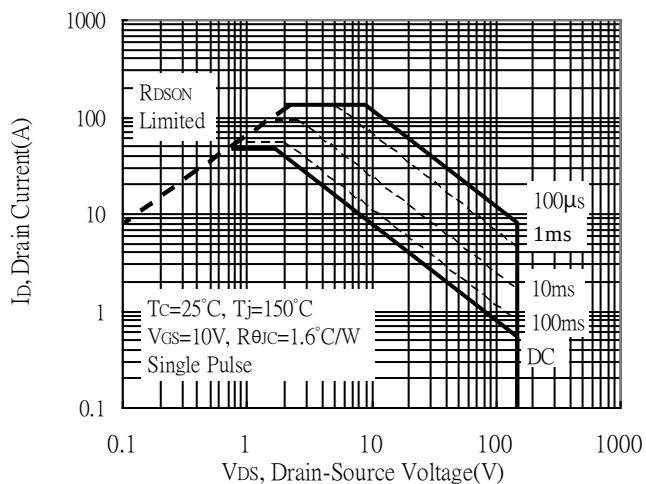
Forward Transfer Admittance vs Drain Current



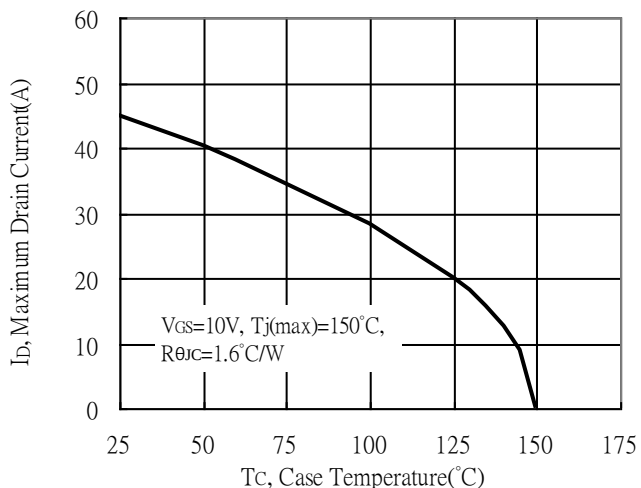
Gate Charge Characteristics



Maximum Safe Operating Area

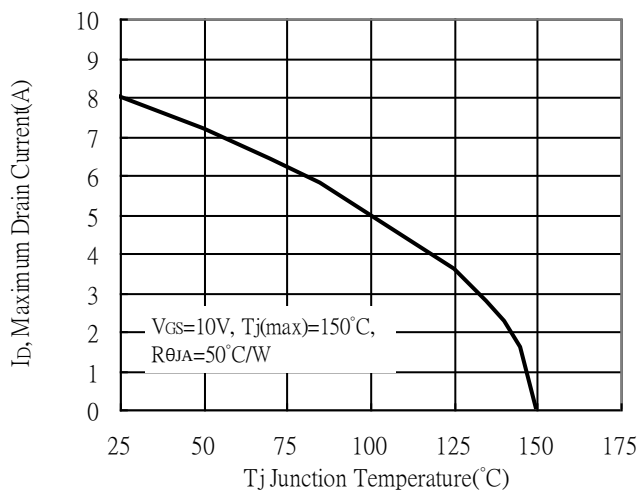


Maximum Drain Current vs Case Temperature

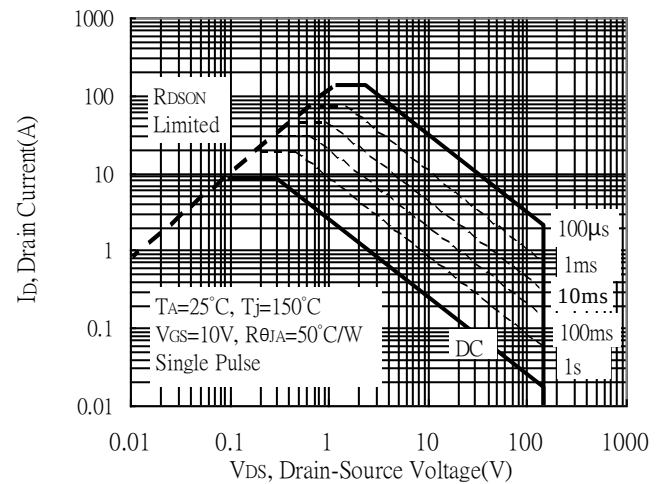


Typical Characteristics (Cont.)

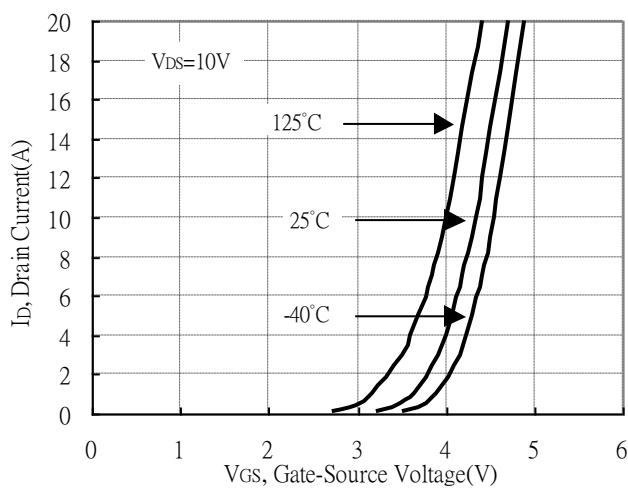
Maximum Drain Current vs Junction Temperature



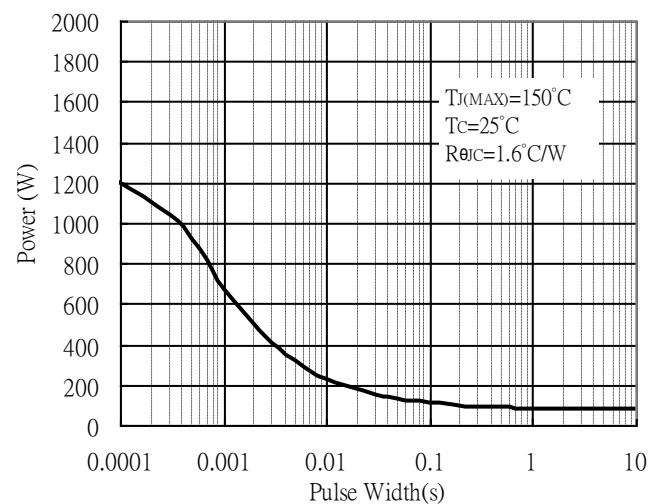
Maximum Safe Operating Area



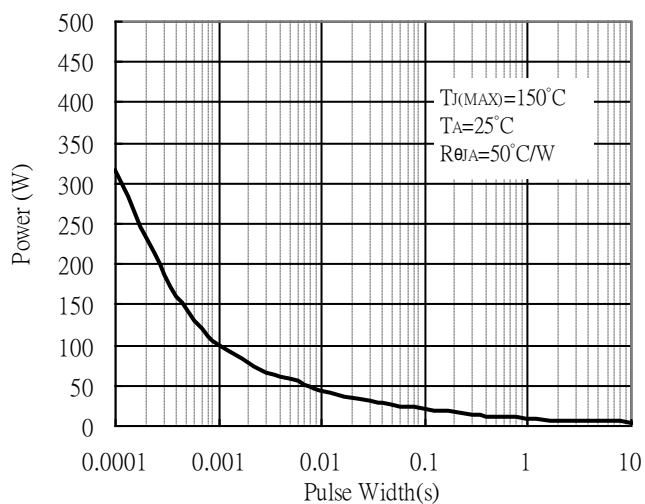
Typical Transfer Characteristics



Single Pulse Power Rating, Junction to Case

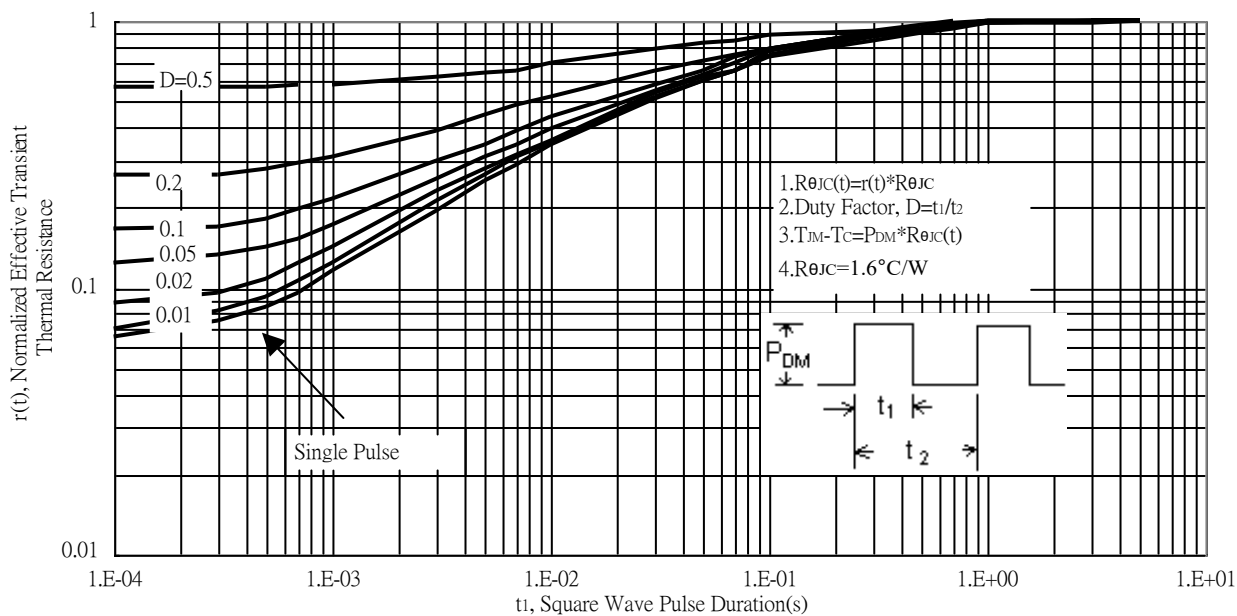


Single Pulse Power Rating, Junction to Case

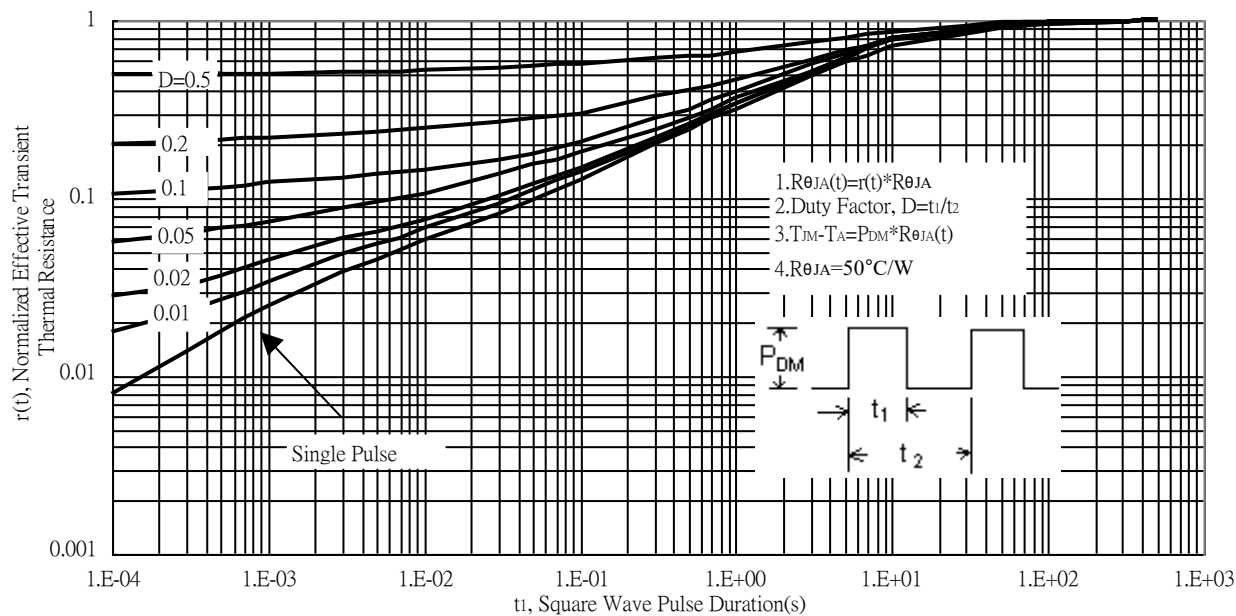


Typical Characteristics (Cont.)

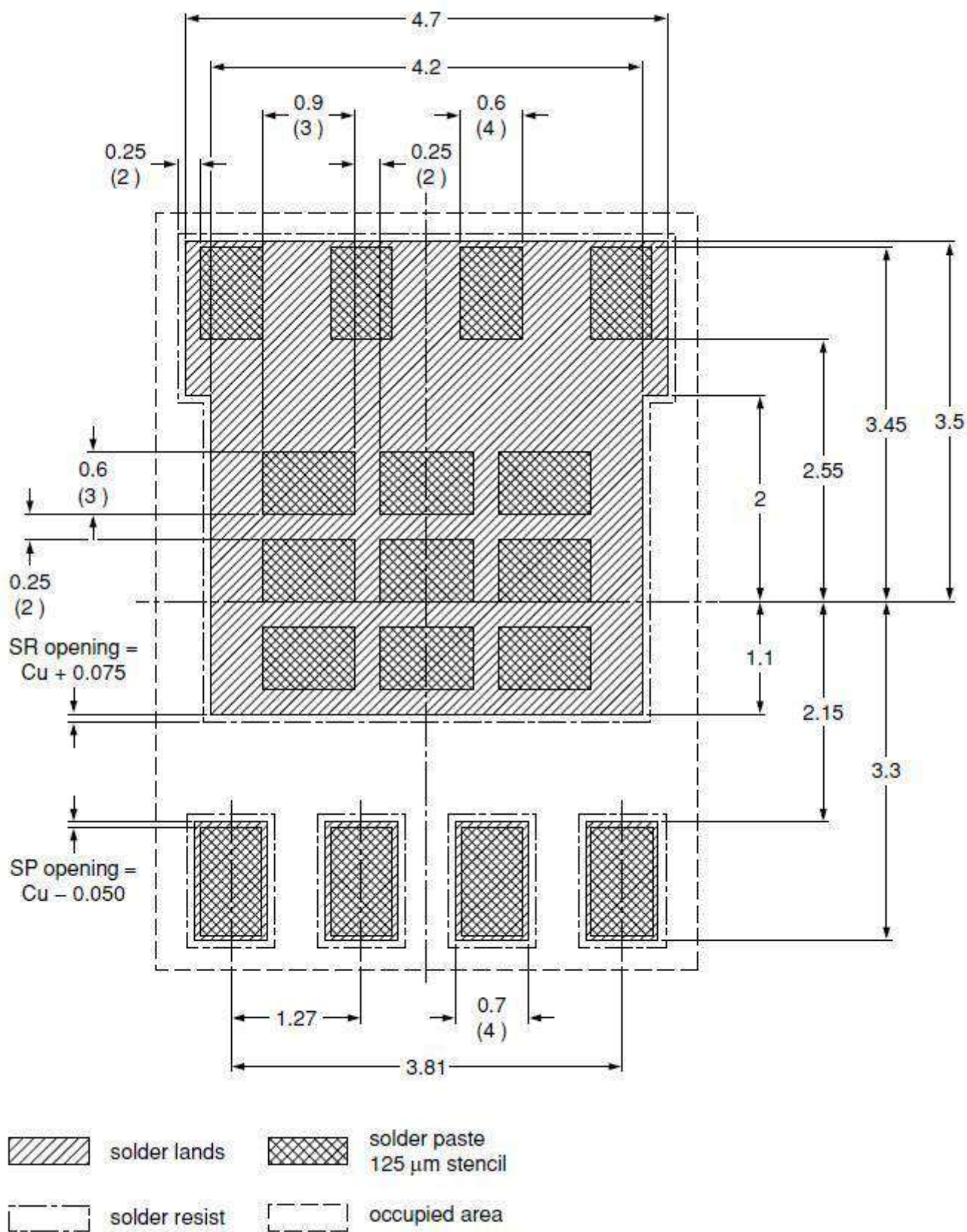
Transient Thermal Response Curves



Transient Thermal Response Curves

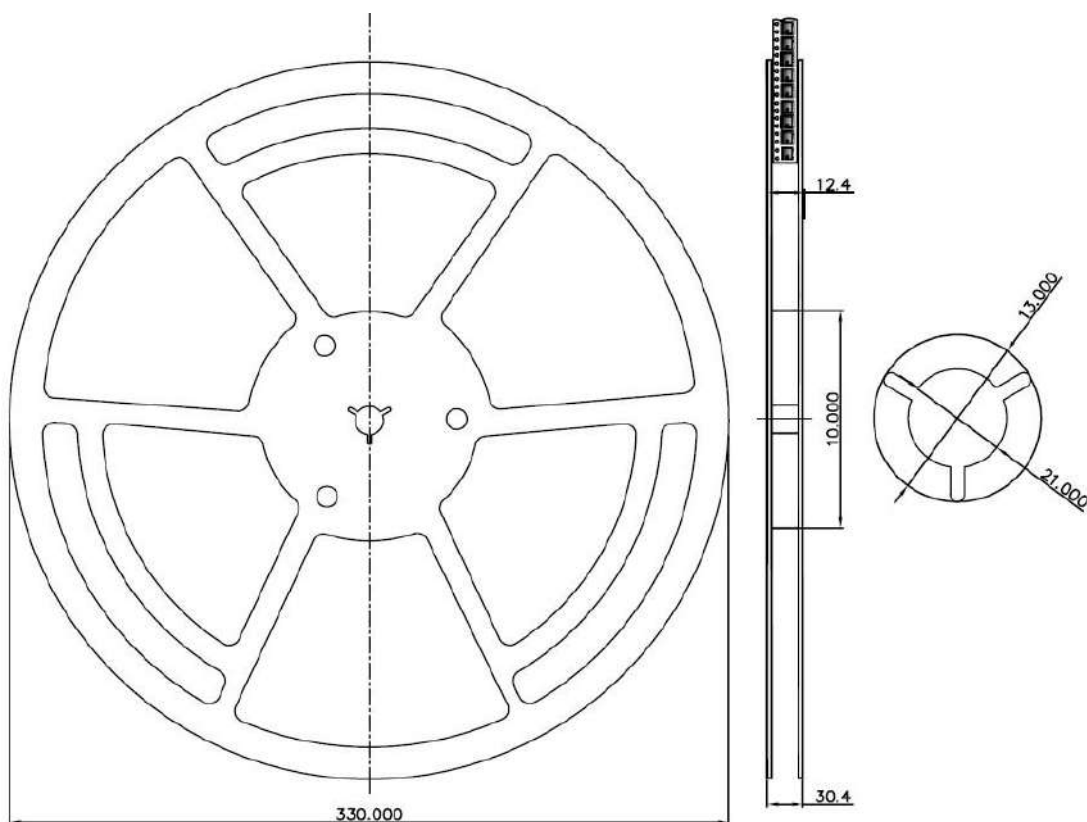


Recommended Soldering Footprint & Stencil Design

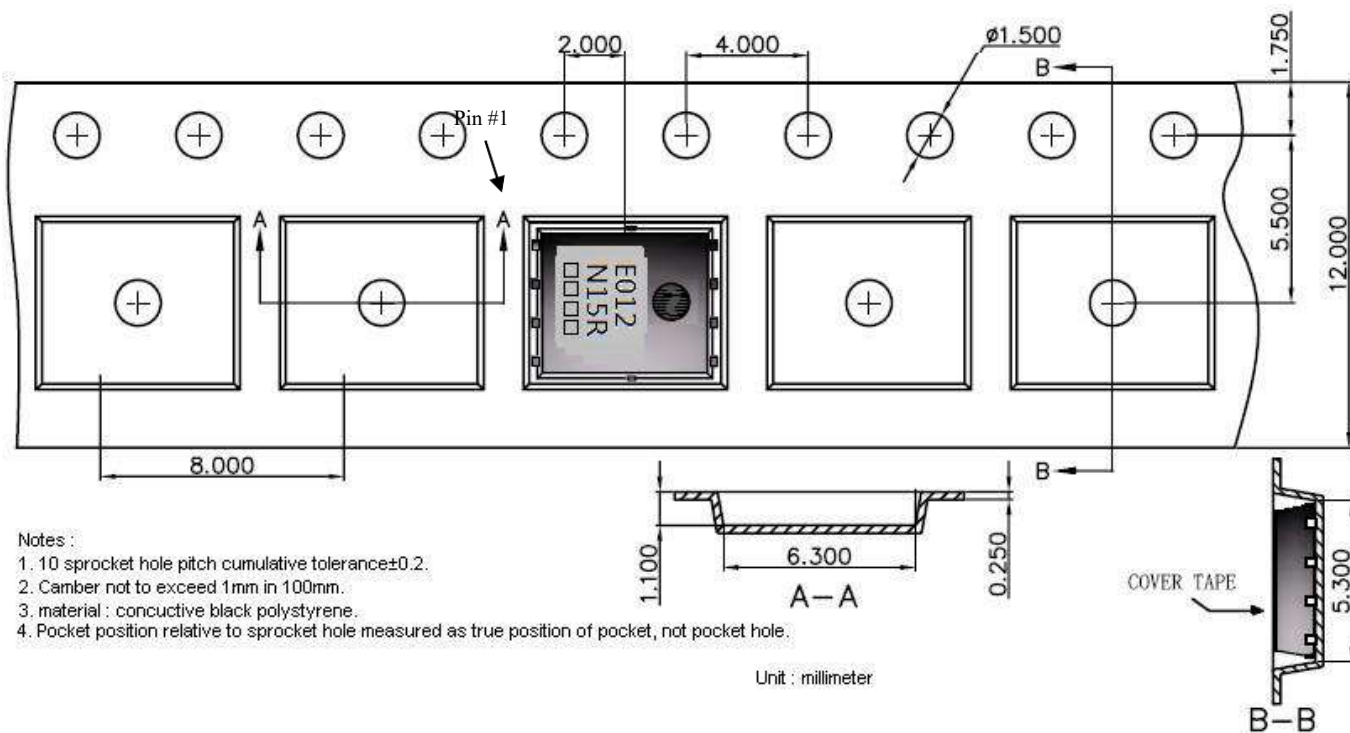


unit : mm

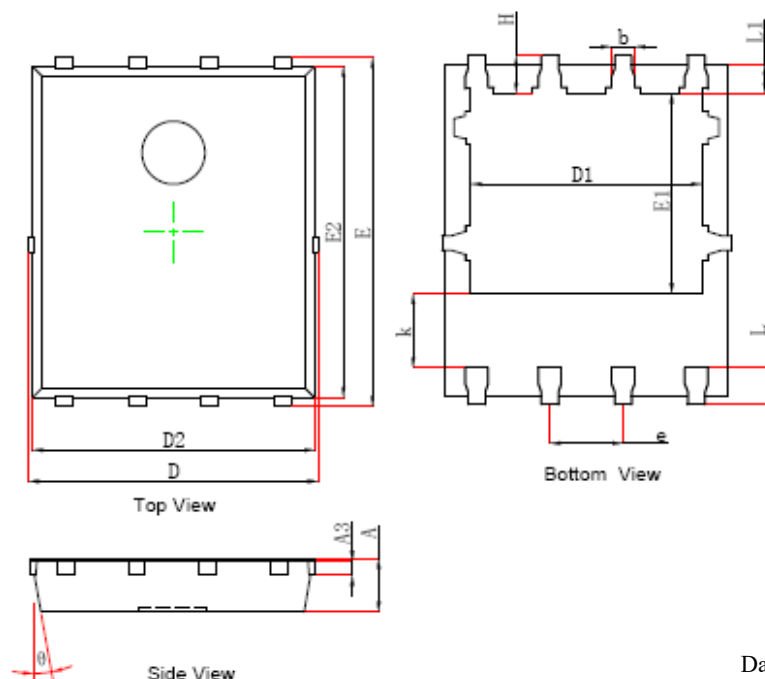
Reel Dimension



Carrier Tape Dimension

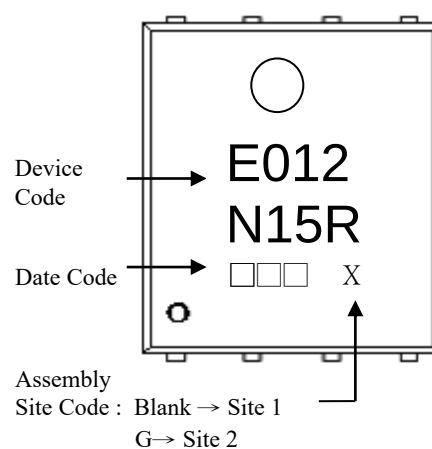


DFN5x6 Dimension



8-Lead DFN5x6 Plastic Package

Marking :



Date Code(counting from left to right) :

- 1st code: year code, the last digit of Christian year
- 2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D, May→E, Jun→F, Jul→G, Aug→H, Sep→J, Oct→K, Nov→L, Dec→M
- 3rd and 4th codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	k	1.100	-	0.043	-
A3	0.200	0.300	0.008	0.012	b	0.330	0.510	0.013	0.020
D	4.944	5.096	0.195	0.201	e	1.270	TYP.	0.050	TYP.
E	5.900	6.126	0.232	0.241	L	0.510	0.711	0.020	0.028
D1	3.670	4.110	0.144	0.162	L1	0.310	0.576	0.012	0.023
E1	3.375	3.780	0.133	0.149	H	0.410	0.726	0.016	0.029
D2	4.800	5.000	0.189	0.197	θ	8°	12°	8°	12°
E2	5.674	5.826	0.223	0.229					